

Amendments to the Specification:

Amend paragraph [0003] (now paragraph [0004]) on page 2 as follows:

[0003] Figs. 1 and 2 diagrammatically depict a prior art ~~susceptor 110~~ susceptor 100, and issues associated therewith which motivated some aspects of the invention. ~~Susceptor 110~~ Susceptor 100 comprises a body 112 which receives a substrate 114 for deposition. Substrate 114 is received within a pocket or recess 116 of susceptor body 112 to elevationally and laterally retain substrate 114 in the desired position.

Amend paragraph [0004] (now paragraph [0005]) on page 2 as follows:

[0004] A particular exemplary system which motivated some of the inventive susceptor designs herein was a lamp heated, thermal deposition system having front and back side radiant heating of the substrate and susceptor for attaining desired temperature during deposition. Fig. 2 depicts a thermal deposition system having at least two radiant heating sources for each side of ~~susceptor 110~~ susceptor 100. Depicted are front side and back side peripheral radiation emitting sources 118 and 120, respectively, and front side and back side radially inner radiation emitting sources 122 and 124, respectively. Incident radiation from sources 118, 120, 122 and 124 typically overlap one another on the susceptor and substrate, creating overlap areas 125. Such can cause an annular region of the substrate corresponding in position to overlap areas 125 to be hotter than other areas of the substrate not so overlapped. Further, the center and periphery of the substrate can be cooler than even the substrate area which is not overlapped due to less than complete or even exposure to the incident radiation.

Amend paragraph [0035] (now paragraph [0036]) on page 13 as follows:

[0035] An exemplary method of depositing an elemental silicon-comprising material over a semiconductor substrate is described initially with reference to Figs. 3 and 4. Such diagrammatically depict a deposition chamber system 10 comprising a chamber 13 having walls 12. A rotatable susceptor 14 retains a semiconductor substrate 16 for deposition within chamber walls 12. Chamber walls 12 comprise first and second infrared radiation transparent walls 18 and 20, respectively. First wall 18 is received below substrate 16, and second wall 20 is received above substrate 16. In the context of this document, a wall which is transparent to infrared radiation passes at least 75% of incident infrared radiation therethrough. By way of example only, exemplary preferred materials include silicon dioxides and sapphire. Further in the context of this document, a "wall" includes all as well as only a portion of any chamber ~~volume-defining~~ volume-defining surface.

Amend paragraph [0037] (now paragraph [0038]) on page 14 as follows:

[0037] At least one plasma generating electrode 30 is received external of chamber 13 proximate second infrared radiation transparent wall 18. In the illustrated and preferred embodiment, at least one plasma generating electrode 32 is received external of chamber 13 proximate first infrared radiation transparent wall 20. The electrodes might be in the form of Rf generating coils, or of other configuration(s). Further in the depicted embodiment, plasma generating electrodes 30 and 32 are received intermediate (between) their respective infrared radiation transparent wall and lamp or lamps. The described system is only exemplary for use in a method of carrying out aspects of the invention, and is only diagrammatic in its representation. Alternate constructions of a chamber or chamber system for carrying out methodical aspects of the invention could of course be utilized, with the concluding method claims ~~not be limited~~ not being limited by the depicted or described apparatus unless language literally apparent in the claim under analysis refers to specific apparatus orientation. For example and by way of example only, any of lamps 22, 24, 26 or 28 might be received remotely from the as-shown positions, with light being directed to and through the transparent walls by one or more reflectors, mirrors or by other

means. Further by way of example only, the depicted plasma generating electrodes 30 and 32 might be fabricated in such a manner as to be removable when not in use, for example when utilizing heat lamps 22, 24, 26 and 28 in a deposition process not employing any plasma generation with electrodes 30 and 32.

Amend paragraph [0053] (now paragraph [0054]) on page 23 as follows:

[0053] Referring to Fig. 9, after feeding of the cleaning gas, an elemental silicon comprising silicon-comprising material 55 is deposited on semiconductor substrate 52 within deposition chamber 50. Exemplary preferred materials are those as described above.

Amend paragraph [0054] (now paragraph [0055]) on page 23 as follows:

[0054] The above processing described but one exemplary implementation of *in situ* cleaning of at least some native oxide from semiconductor from a semiconductor substrate within a deposition chamber within which an elemental silicon-comprising material deposition will occur. By way of example only, Fig. 10 is utilized to describe another method of depositing an elemental silicon-comprising material over a semiconductor substrate. Fig. 10 diagrammatically depicts a deposition tool 60 adapted for depositing elemental silicon-comprising material. Typically, such would be configured for subatmospheric pressure deposition, and is depicted as comprising a load lock chamber 62, a cleaning chamber 64 and three deposition chambers 66, 68 and 70. Of course, more or fewer chambers could be utilized. A preferred transfer chamber 72 is centrally positioned relative to the stated other chambers for transferring substrates among the various chambers in an inert, or at least sealed, environment.